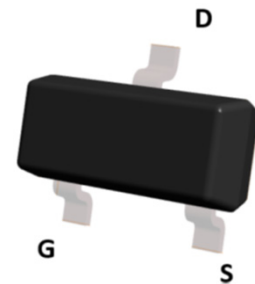
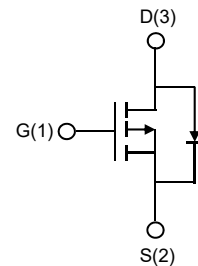
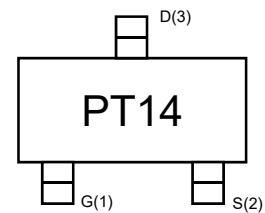


Description

The MOSFET provide the best combination of fast switching , low on-resistance and cost-effectiveness.

- Trench Power MV MOSFET technology
- Voltage controlled small signal switch
- Low input Capacitance
- Fast Switching Speed
- Low Input / Output Leakage


Top View

Circuit Diagram

Marking (Top View)

| MOSFET Product Summary | | |
|------------------------|-----------------------|----------|
| $V_{DS}(V)$ | $R_{DS(on)}(m\Omega)$ | $I_D(A)$ |
| -12 | 32@ $V_{GS} = -4.5V$ | -4.0 |
| | 42@ $V_{GS} = -2.5V$ | |
| | 63@ $V_{GS} = -1.8V$ | |

Applications

- Battery operated systems
- Solid-state relays
- Direct logic-level interface: TTL/CMOS

Absolute maximum rating@25°C

| Rating | Symbol | Value | Units |
|--|-------------------|----------|-------|
| Drain-source Voltage | V_{DS} | -12 | V |
| Gate-source Voltage | V_{GS} | ± 12 | V |
| Drain Current | I_D | -4.0 | A |
| Pulsed Drain Current | I_{DM} | -35 | A |
| Total Power Dissipation | $T_A=25^\circ C$ | 0.83 | W |
| | $T_A=125^\circ C$ | 0.17 | |
| Avalanche Energy, Single Pulse | E_{AS} | 27.31 | mJ |
| Junction and Storage Temperature Range | T_J, T_{STG} | -55~+150 | °C |

Electrical characteristics per line@25°C (unless otherwise specified)

| Parameter | Symbol | Conditions | Min. | Typ. | Max. | Units |
|-----------------------------------|--------------|---|------|------|-----------|------------|
| OFF Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS} = 0V, I_D = -250\mu A$ | -12 | - | - | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = -12V, V_{GS} = 0V$ | - | - | -1 | μA |
| Gate-Body Leakage Current | I_{GSS} | $V_{GS} = \pm 12V, V_{DS} = 0V$ | - | - | ± 100 | nA |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = -250\mu A$ | -0.4 | - | -1.0 | V |
| Static Drain-Source On-Resistance | $R_{DS(on)}$ | $V_{GS} = -4.5V, I_D = -4.3A$ | - | 32 | 45 | m Ω |
| | | $V_{GS} = -2.5V, I_D = -2.5A$ | - | 42 | 60 | |
| | | $V_{GS} = -1.8V, I_D = -2.0A$ | - | 63 | 100 | |
| Dynamic Parameters | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS} = -10V, V_{GS} = 0V,$ $f = 1MHz$ | - | 859 | - | pF |
| Output Capacitance | C_{oss} | | - | 122 | - | |
| Reverse Transfer Capacitance | C_{rss} | | - | 106 | - | |
| Switching Parameters | | | | | | |
| Turn-on Delay Time | $t_{D(on)}$ | $V_{Gen} = -4.5V, V_{DD} = -10V,$ $R_G = 1\Omega, I_D = -3.3A$ | - | 6.0 | - | ns |
| Turn-on Rise Time | t_r | | - | 22.5 | - | |
| Turn-off Delay Time | $t_{D(off)}$ | | - | 29 | - | |
| Turn-off Fall Time | t_f | | - | 35 | - | |

Typical Characteristics

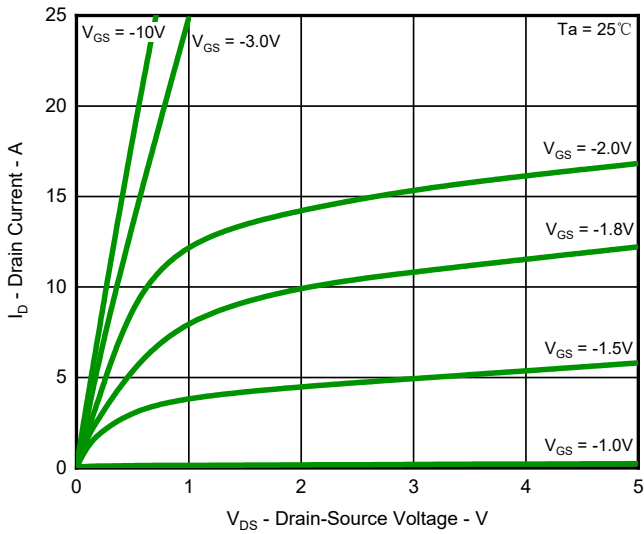


Fig.1 Output Characteristics

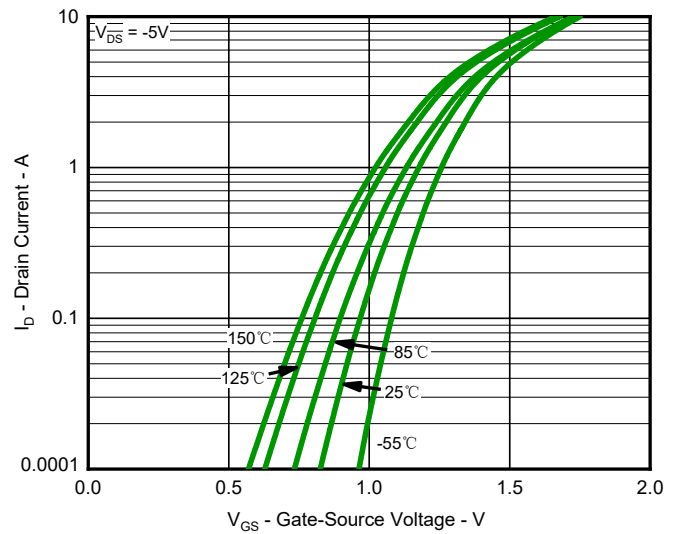


Fig.2 Typical Transfer Characteristic

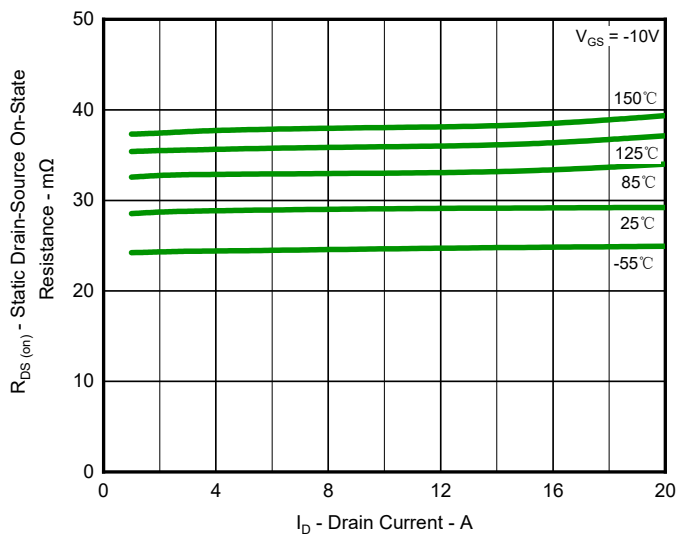


Fig.3 Typical On-Resistance vs Drain Current and Temperature

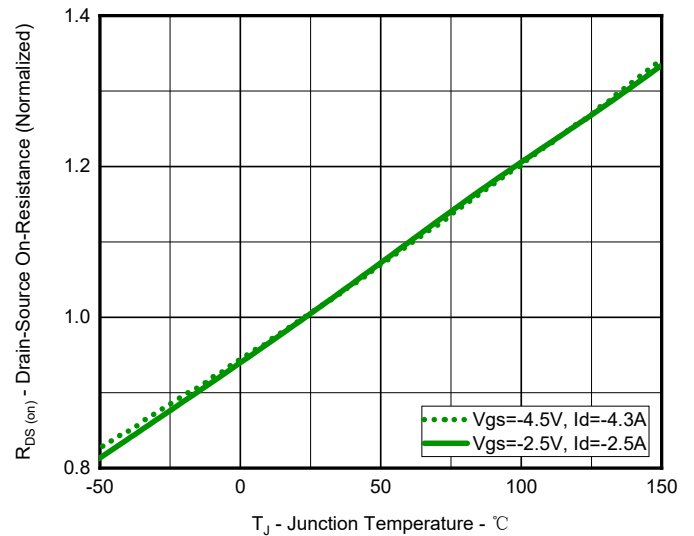


Fig.4 On-Resistance Variation with Temperature(I)

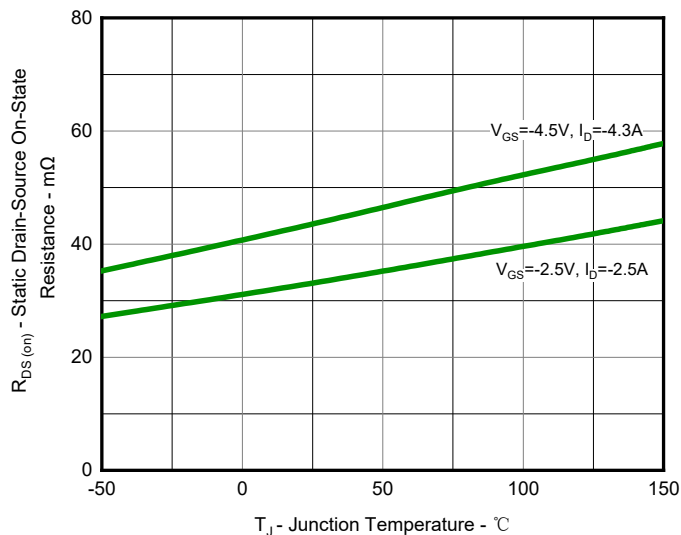


Fig.5 On-Resistance Variation with Temperature(II)

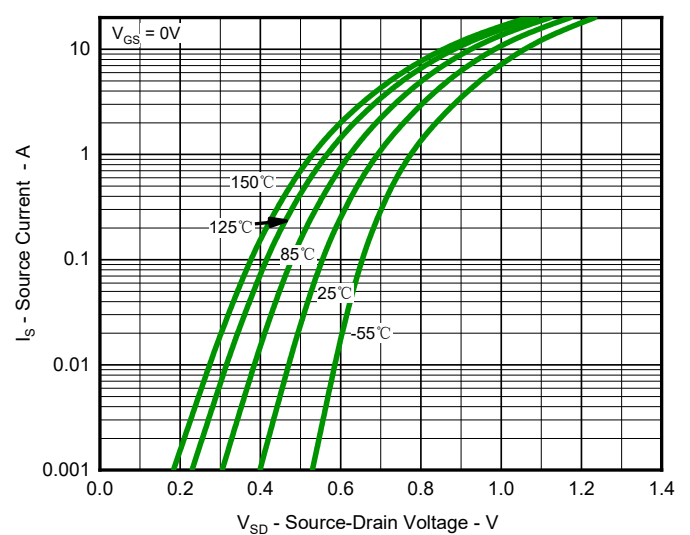


Fig.6 Diode Forward Voltage vs. Current

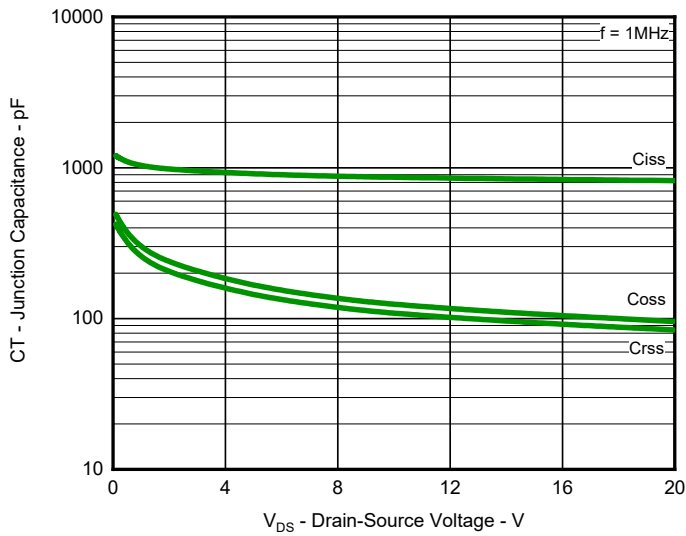


Fig.7 Typical Junction Capacitance

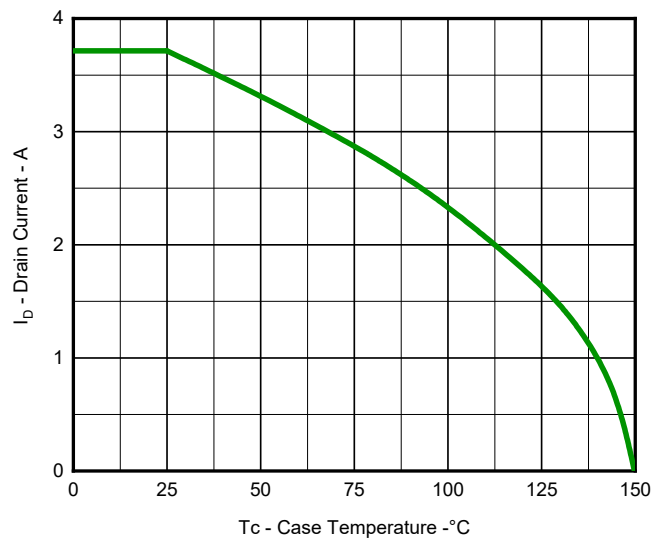


Fig.8 Maximum Drain Current vs. Case Temperature

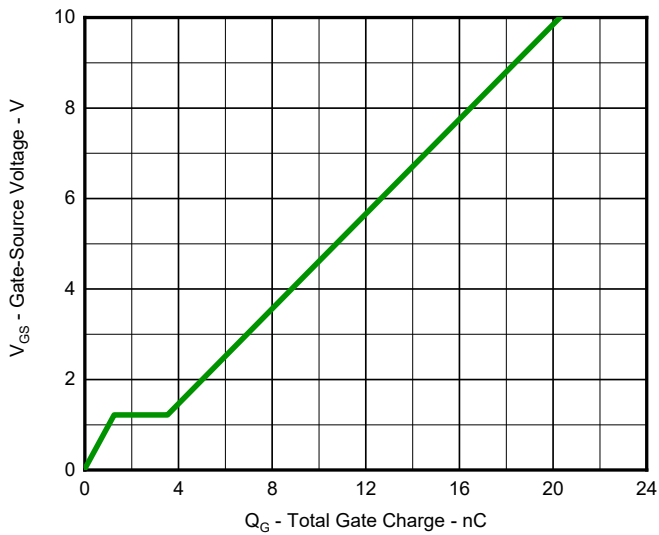


Fig.9 Gate Charge Characteristics

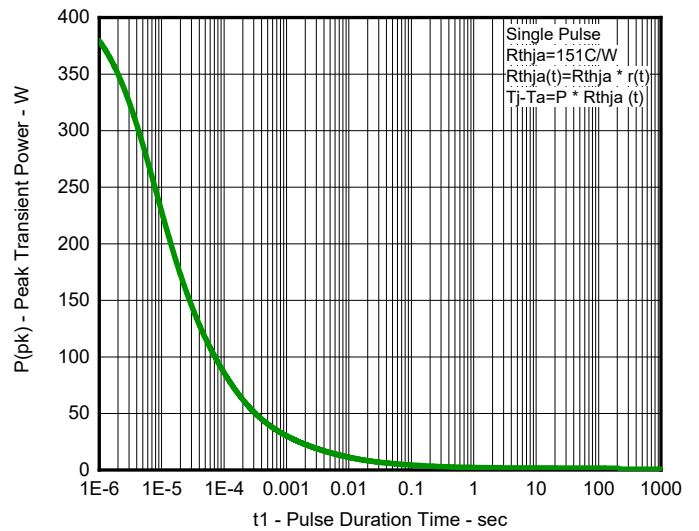


Fig.10 Single Pulse Maximum Power Dissipation

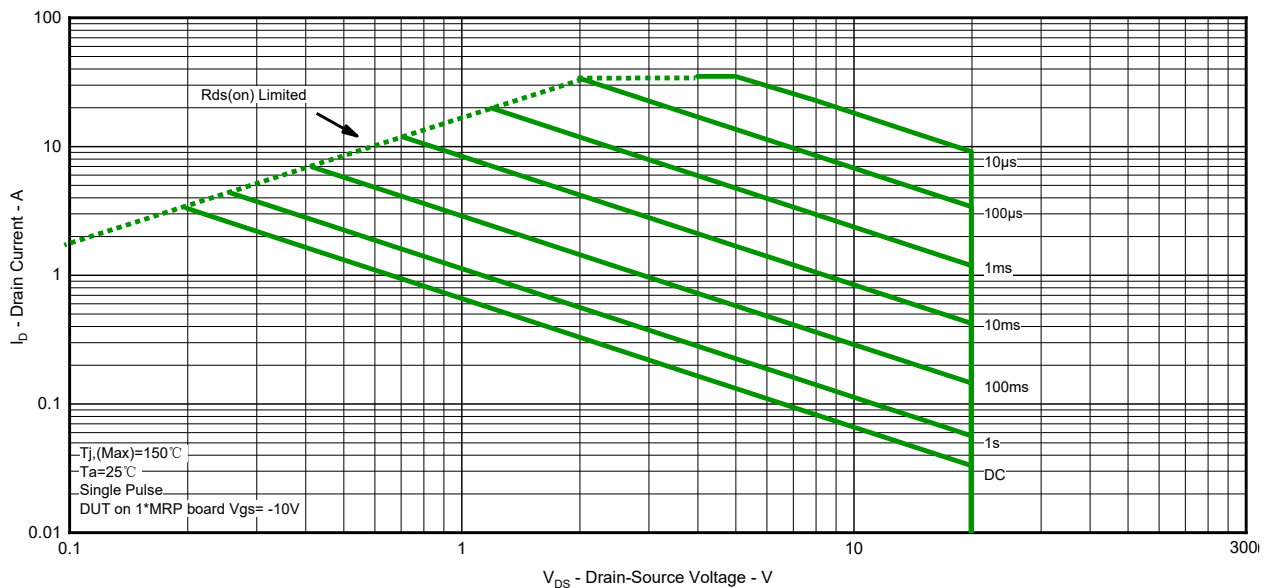


Fig.11 Safe Operation Area

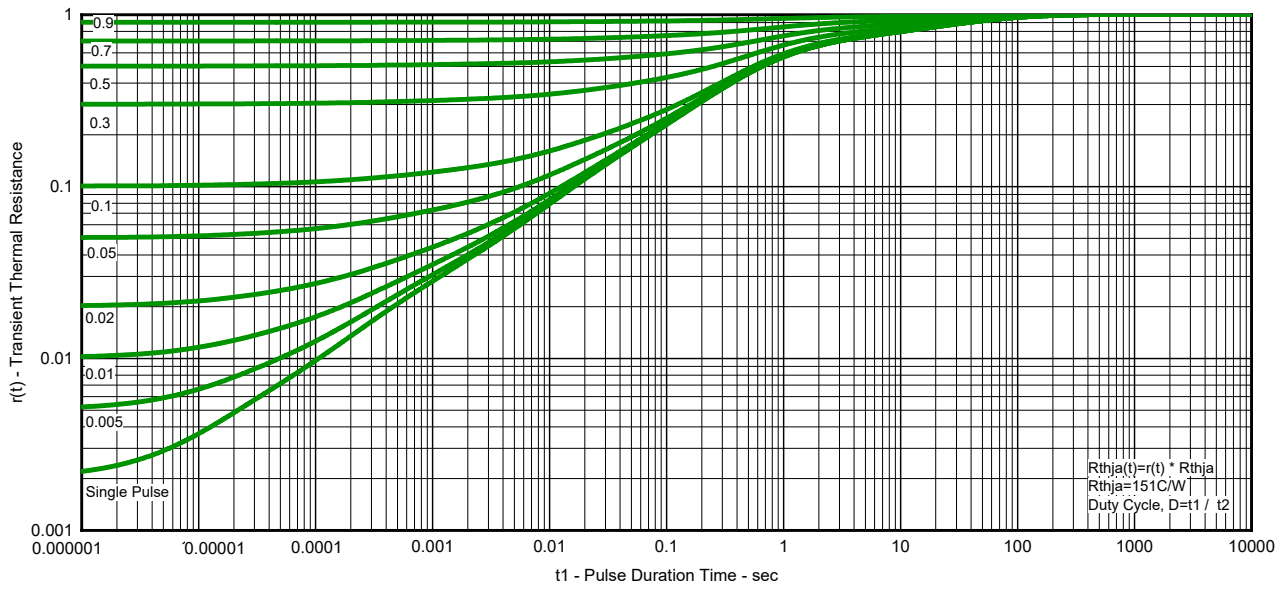
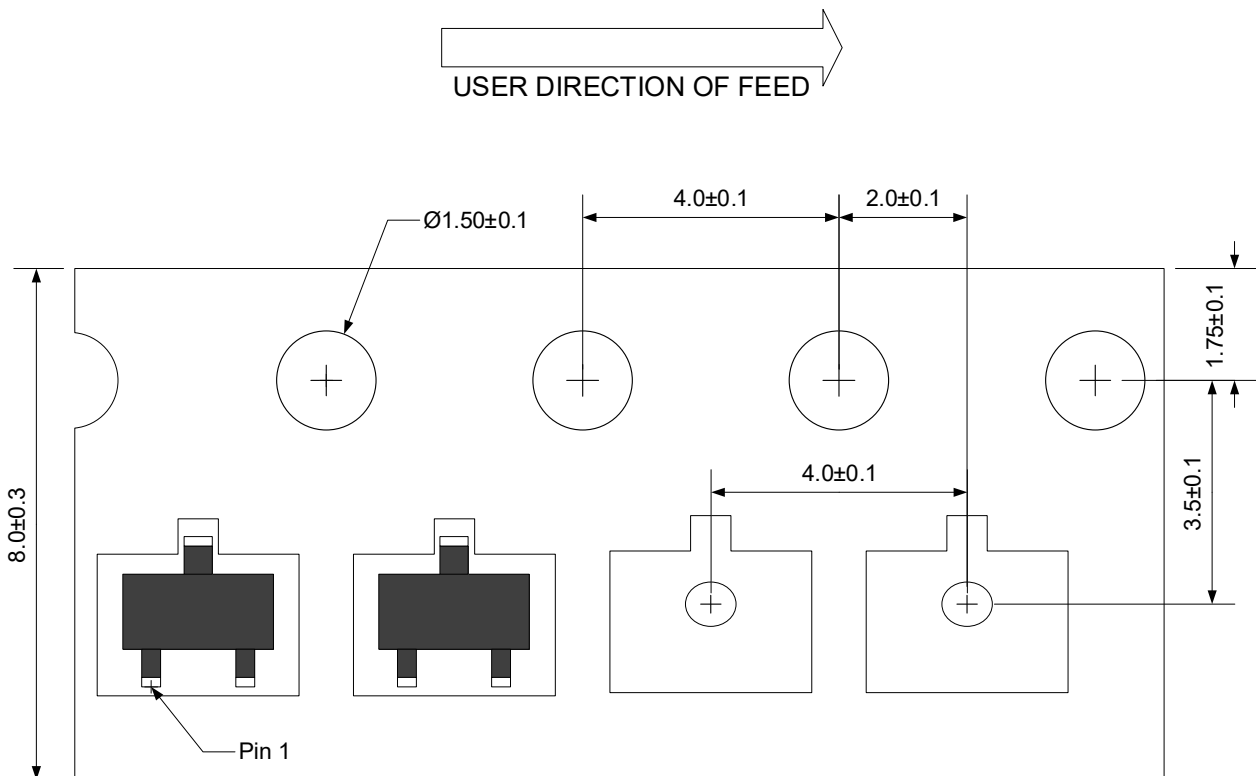


Fig.12 Transient Thermal Resistance

Ordering information

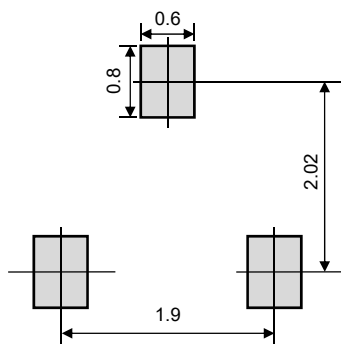
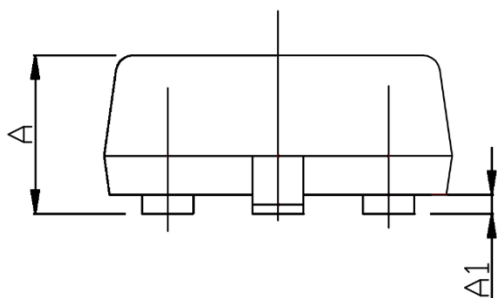
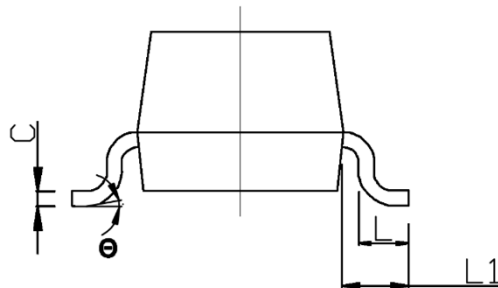
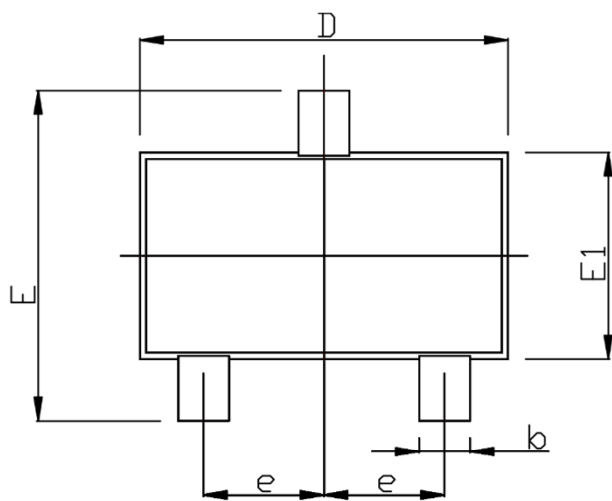
| Device | Package | Reel | Shipping |
|----------|------------------|------|--------------------|
| PPMT12V4 | SOT-23 (Pb-Free) | 7" | 3000 / Tape & Reel |

Load with information



Unit:mm

Product dimension (SOT-23)




Suggested PCB Layout

Unit:mm

| Dim | Millimeters | | Inches | |
|----------|-------------|------|-----------|-------|
| | Min | Max | Min | Max |
| A | - | 1.35 | - | 0.053 |
| A1 | 0.04 | 0.15 | 0.002 | 0.006 |
| b | 0.30 | 0.50 | 0.012 | 0.020 |
| c | 0.08 | 0.21 | 0.003 | 0.008 |
| D | 2.72 | 3.12 | 0.107 | 0.123 |
| E | 2.10 | 2.64 | 0.083 | 0.104 |
| E1 | 1.10 | 1.50 | 0.043 | 0.059 |
| e | 0.95 BSC | | 0.037 BSC | |
| L | 0.20 | 0.48 | 0.008 | 0.019 |
| L1 | 0.50 | 0.60 | 0.020 | 0.024 |
| θ | 0° | 8° | 0° | 8° |


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